



MCQ set#4:Si Microfabrication (Continue)

Choose the most proper answer:

1. is considered as the most expensive micromechanical process:
a) Etching
b) Lift-off technique
c) Lithography <
d) Masking
2. Lithography is used for:
a) Forming resist layers on the substrate <
b) Cutting tool
c) Forming electric bonds
d) None of the above
3. Types of lithography:
a) Photolithography
b) X-ray lithography
c) E-beam lithography
d) All of the above <
4. Types of photoresist:
a) Positive
b) Negative
c) a & b <
d) None of the above
5. In X-ray lithography, the X-ray absorber is usually:
a) Silver
b) Gold <
c) Aluminum
d) None of the above
6. is projecting electron beam directing on photoresist of the wafer :
a) E-beam lithography <
b) Light emitting
c) Electron beam gun
d) Radar beam
7. The electron gun is used in lithography because it is..... :
a) Inexpensive
b) Accurate <
c) Doesn't require high voltage
d) Not e of the above
- 8.....Used for removing desired areas of the photo resist from the substrate:
a) LIGA
b) Lithography
c) Etching <
d) Not e of the above
9. Types of etching are.....:
a) Wet isotropic
b) Wet anisotropic
c) Dry
d) All of the above <
10. The most widely used anisotropic etchant is/are.....:
a) KOH
b) KCl
c) NaOH
d) a&c <
11. Etching is always anisotropic if the material is.....:
a) Crystalline <
b) Polycrystalline
c) Amorphous
d) None of the above
12.is an Etch stop technique.
a) Wet isotropic etching.
b) Wet anisotropic etching.
c) Electrochemical etching. <
d) Physical sputter etching.
- 13.....is the etching through chemical or physical interaction between ions:
a) Wet isotropic etching
b) Wet anisotropic etching
c) Dry etching <
d) None of the above
14. Methods of dry etching are:
a) Physical sputter etching
b) Chemical plasma etching
c) Combined chemical/physical etching
d) All of the above <
15. is used for metals that are hard to etch:
a) Lift-off technique <
b) Combined physical/chemical etching
c) Physical sputter etching
d) Chemical plasma etching